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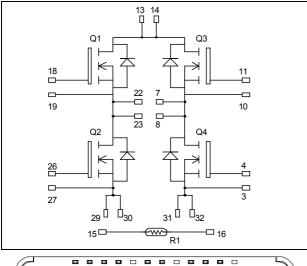
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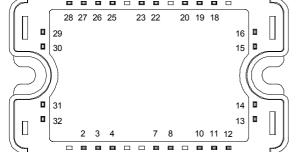
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Full - Bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		500	V
т	I_D Continuous Drain Current $T_c = 25$ $T_c = 80$		46	
пр			34	А
I _{DM}	Pulsed Drain current		184	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		90	mΩ
PD	Maximum Power Dissipation $T_c = 25^{\circ}C$		357	W
I _{AR}	Avalanche current (repetitive and non repetitive)		46	А
E _{AR}	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy		2500	111J

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{DSS} = 500V$ $R_{DSon} = 75m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}\text{C}$ $I_D = 46\text{A} @ \text{Tc} = 25^{\circ}\text{C}$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
 - Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^{\circ}C$			100	μA
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125^{\circ}C$			500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 23A$		75	90	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$	3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		5600		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		1200		pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		90		
Qg	Total gate Charge	$V_{GS} = 10V$		123		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 250V$		33		nC
Q_{gd}	Gate – Drain Charge	$I_{\rm D} = 46 {\rm A}$		65		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		18		
T _r	Rise Time	$V_{GS} = 15V$ $V_{GS} = 222V$		35		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 333V$ $I_D = 46A$		87		
$T_{\rm f}$	Fall Time	$R_G = 5\Omega$		77		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		755		
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 46A, R_G = 5\Omega$		726		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		1241		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 46A, R_G = 5\Omega$		846		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Is	Continuous Source current		$Tc = 25^{\circ}C$			46	А	
	(Body diode)		$Tc = 80^{\circ}C$			34	A	
V _{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -46A$				1.3	V	
dv/dt	Peak Diode Recovery 1					15	V/ns	
t _{rr}	Reverse Recovery Time	X 464	$T_j = 25^{\circ}C$		233		ns	
۹rr	Reverse Receivery Time	$I_{\rm S} = -46A$ $V_{\rm R} = 333V$	$T_j = 125^{\circ}C$		499		115	
Q _{rr}	Reverse Recovery Charge	$di_{\rm S}/dt = 100 {\rm A}/{\rm \mu s}$	$T_j = 25^{\circ}C$		1.9		μC	
Qrr	Reverse Recovery Charge		$T_{i} = 125^{\circ}C$		5.7		μ	

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. $I_S \le -46A$ di/dt $\le 700A/\mu s$ $V_R \le V_{DSS}$ $T_j \le 150^{\circ}C$



Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance				0.35	°C/W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
TJ	Operating junction temperature range		-40		150		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

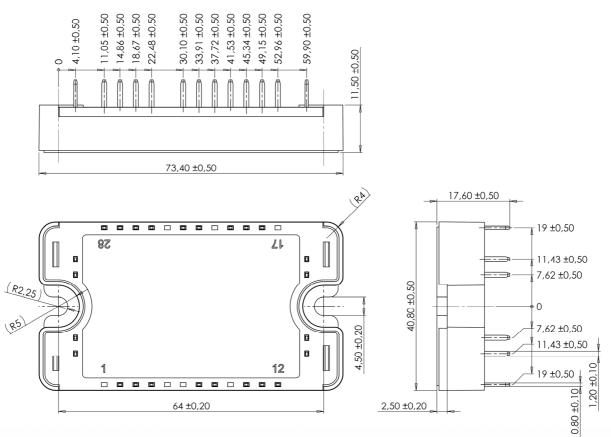
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$= \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

 R_T

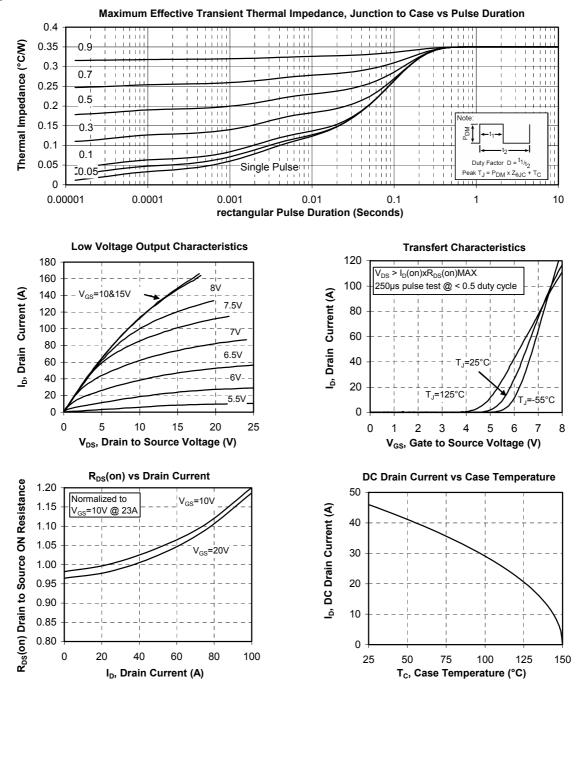


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

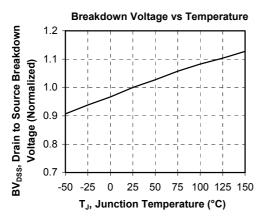
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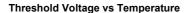


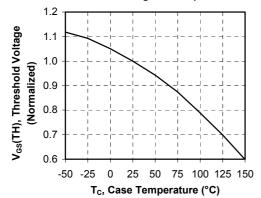
Typical Performance Curve

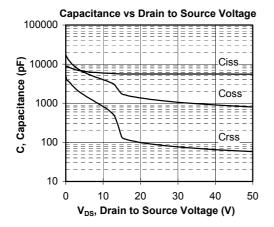


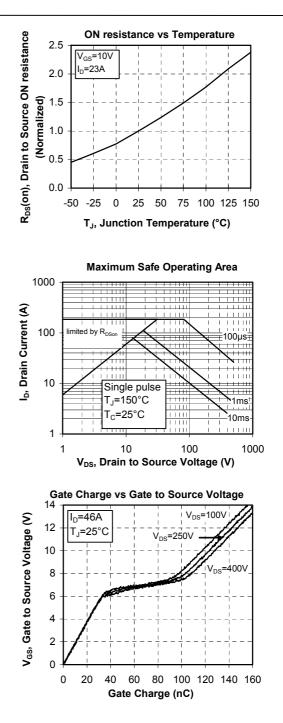








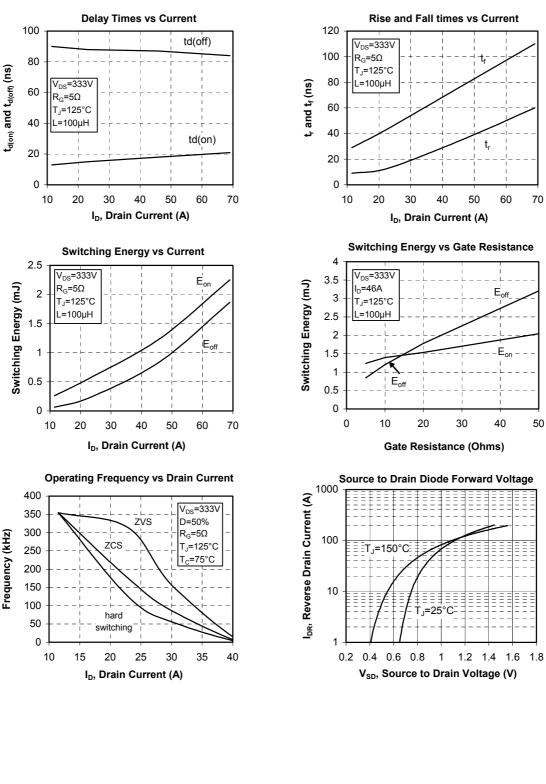






Frequency (kHz)

APTM50HM75FT3G



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